

# Schottky Barrier Diodes

These Schottky barrier diodes are designed for high speed switching applications, circuit protection, and voltage clamping. Extremely low forward voltage reduces conduction loss. Miniature surface mount package is excellent for hand held and portable applications where space is limited.

- Extremely Fast Switching Speed
- Low Forward Voltage — 0.35 Volts (Typ) @  $I_F = 10 \text{ mAdc}$
- Device Marking: JV

We declare that the material of product compliance with RoHS requirements.

## LBAT54HT1G



### ORDERING INFORMATION

Device	Marking	Shipping
LBAT54HT1G	JV	3000/Tape & Reel
LBAT54HT3G	JV	10000/Tape & Reel

### MAXIMUM RATINGS ( $T_J = 125^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Reverse Voltage	$V_R$	30	V

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25^\circ\text{C}$	PD	200	mW
Derate above $25^\circ\text{C}$		1.57	mW/ $^\circ\text{C}$
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	635	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	$T_J, T_{stg}$	150	$^\circ\text{C}$

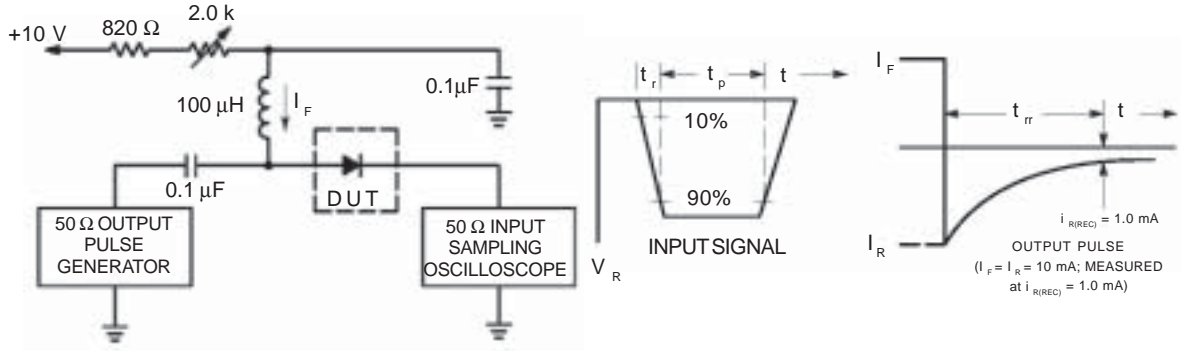
\* FR-4 Minimum Pad



### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted) (EACH DIODE)

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Breakdown Voltage ( $I_R = 10 \mu\text{A}$ )	$V_{(BR)R}$	30	—	—	Volts
Total Capacitance ( $V_R = 1.0 \text{ V}$ , $f = 1.0 \text{ MHz}$ )	$C_T$	—	7.6	10	pF
Reverse Leakage ( $V_R = 25 \text{ V}$ )	$I_R$	—	0.5	2.0	$\mu\text{Adc}$
Forward Voltage ( $I_F = 0.1 \text{ mAdc}$ )	$V_F$	—	0.22	0.24	Vdc
Forward Voltage ( $I_F = 0.15 \text{ mAdc}$ )	$V_F$	—	0.24	0.26	Vdc
Forward Voltage ( $I_F = 0.15 \text{ mAdc}$ , $T_J = -25^\circ\text{C}$ )	$V_F$	—	0.33	0.35	Vdc
Forward Voltage ( $I_F = 0.15 \text{ mAdc}$ , $T_J = 85^\circ\text{C}$ )	$V_F$	—	0.16	0.18	Vdc
Forward Voltage ( $I_F = 30 \text{ mAdc}$ )	$V_F$	—	0.41	0.5	Vdc
Forward Voltage ( $I_F = 100 \text{ mAdc}$ )	$V_F$	—	0.52	1.0	Vdc
Reverse Recovery Time ( $I_F = I_R = 10 \text{ mAdc}$ , $I_{R(REC)} = 1.0 \text{ mAdc}$ , Figure 1)	$t_{rr}$	—	—	5.0	ns
Forward Voltage ( $I_F = 1.0 \text{ mAdc}$ )	$V_F$	—	0.29	0.32	Vdc
Forward Voltage ( $I_F = 10 \text{ mAdc}$ )	$V_F$	—	0.35	0.40	Vdc
Forward Current (DC)	$I_F$	—	—	200	mAdc
Repetitive Peak Forward Current	$I_{FRM}$	—	—	300	mAdc
Non-Repetitive Peak Forward Current ( $t < 1.0 \text{ s}$ )	$I_{FSM}$	—	—	600	mAdc

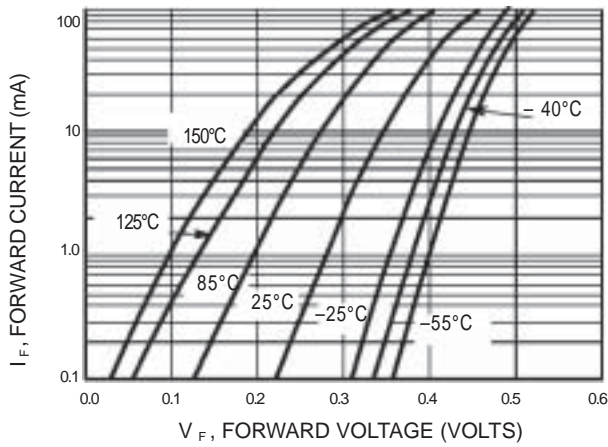
**LBAT54HT1G**



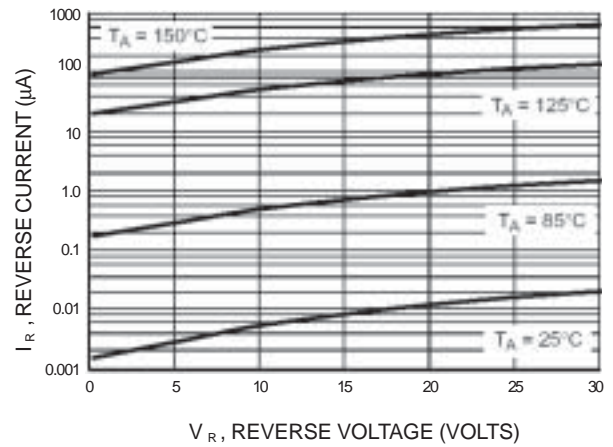
- Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current ( $I_F$ ) of 10mA.  
 2. Input pulse is adjusted so  $I_{R(peak)}$  is equal to 10mA.  
 3.  $t_p \gg t_{rr}$

**Figure 1. Recovery Time Equivalent Test Circuit**

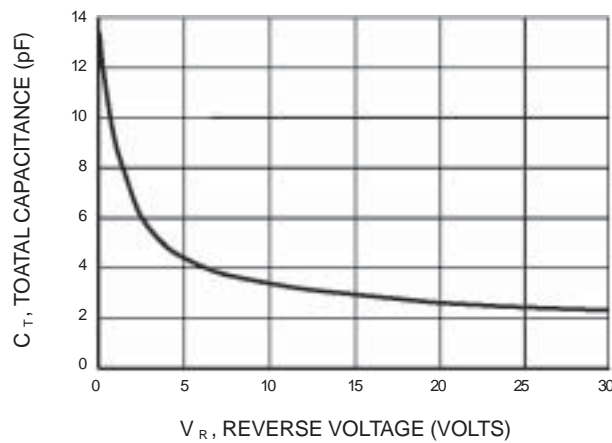
**TYPICAL CHARACTERISTICS**



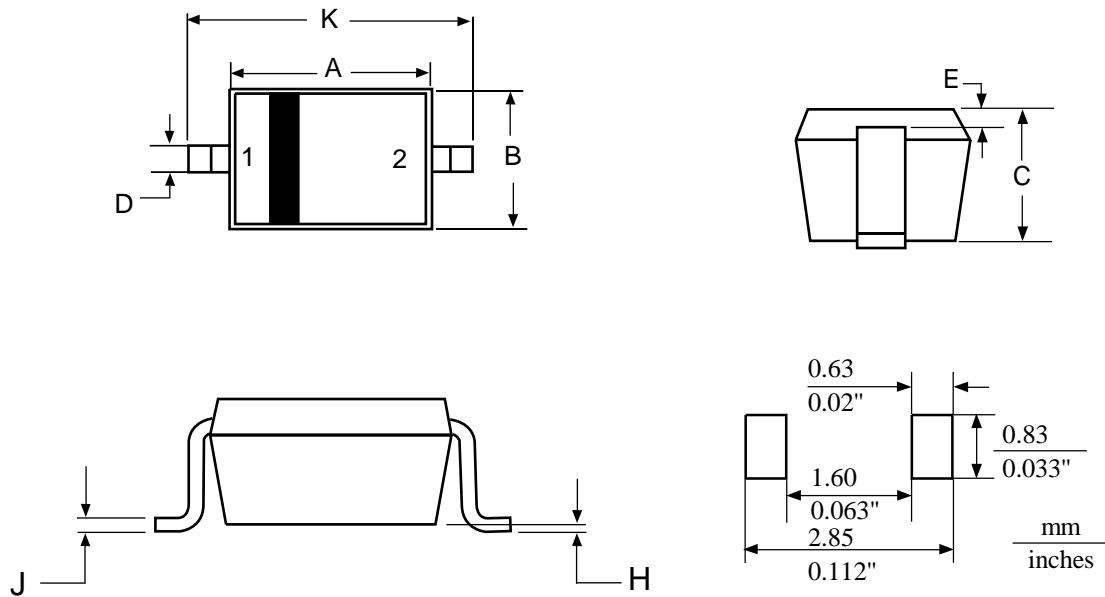
**Figure 2. Forward Voltage**



**Figure 3. Leakage Current**



**Figure 4. Total Capacitance**

**LBAT54HT1G**
**SOD-323**

**NOTES:**

1. DIMENSIONING AND TOLERANCING  
PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.60	1.80	0.063	0.071
B	1.15	1.35	0.045	0.053
C	0.80	1.00	0.031	0.039
D	0.25	0.40	0.010	0.016
E	0.15 REF		0.006 REF	
H	0.00	0.10	0.000	0.004
J	0.089	0.177	0.0035	0.0070
K	2.30	2.70	0.091	0.106

PIN:1:CATHODE  
2:ANODE